	9:00		U. Schröder	Namlab	Welcome
			High k MIM Capacitor		
1	9:20	0:20	K. Frohlich	U. Bratislava	Low EOT TiO_2 based MIM structures for capacitor application
2	9:40	0:20	A. Krause	Namlab	Electrical and physical characterization of CaTiO MIM capacitors
3	10:00	0:20	S. Knebel	Namlab	Leakage current and lifetime evaluation of ZrO based capacitors
4	10:20	0:20	S. Riedel	CNT	2D/3D capacitors for STO based MIM applications
	00:20		Coffee break		
			Non volatile memory		
5	11:00	0:20	J. Müller	CNT Dresden	Electrical characterization of HfO based ferroelectric devices
6	11:20	0:20	D. Martin	Namlab	Thickness dependence of ferroelectric HfO based materials
7	11:40	0:20	I. Müller	RWTH Aachen	Characterization of ferroelectric HfO based materials
8	12:00	0:20	A. Kersch	Hochschule München	Structural phases of HfO_2 and ZrO_2 from ab initio point of view
	01:10		Lunch at MPI - PKS		
			RRAM/Device		
9	13:30	0:20	E. Erben	Global Foundries	High k in 3x nm replacment gate
10	13:50	0:20	M. Reiners	FZ Jülich	Atomic layer Deposition and Characterization of TiO_{2-x} Thin Films for Resistive
11	14:10	0:20	T. Bertaud	IHP Frankfurt/O	Resistive switching characteristics of HfO2-based 1T1R cells
12	14:30	0:40	H. Mähne	Namlab	Resistive switching of PVD vs ALD NbO based cells
	00:20		Coffee break		
			Solar applications		
13	15:10	0:20	M. Knaut/I. Dirnstorfer	IHM/Namlab	TiO_2 Electrodes for dye sensitized solar cells
14	15:30	0:20	D. Linaschke	FhG IWS	Low cost AlOx deposition by Spin coating for passivation layers
15	15:50	0:20	J. Heitmann	Freiberg	Ge nanocrystal formation in ZrO2 by deposition of GeZrO/ZrO2 superlattices
			ALD application		
16	16:10	0:20	Massimo	Cottbus	ALD of oxides on oxidic substrates investigated by in-situ photoemission
17	16:30	0:20	J. Niinistö	U. Helsinki	Novel ALD processes for depositing NbO thin films
	16:50		End		